

AMENDMENTS TO THE CLAIMS

1-19. (Cancelled)

20. (Currently Amended) A method of producing a crystalline substrate based device comprising:

providing a wafer comprising a semiconductor microstructure including a semiconductor substrate;

providing a spacer at a wafer level, said spacer defining at least one cavity extending entirely therethrough; ~~and~~

adhesively sealing to said wafer at least one transparent packaging layer and said spacer onto said semiconductor substrate over said microstructure and at least partially spaced therefrom, thereby to define at least one gap at said at least one cavity between said microstructure and said at least one packaging layer;

forming a multiplicity of electrical contacts along surfaces of said at least one packaging layer which define edges of individual packaged devices; and

subsequently dicing said wafer into said individual packaged devices,

wherein said spacer is formed as a piece separate from said substrate ~~and from said at least one packaging layer.~~

21. (Cancelled)

22. (Previously Presented) A method of producing a crystalline substrate based device according to claim 20 and wherein said adhesively sealing comprises using Epoxy to seal said at least one transparent packaging layer and said spacer onto said substrate.

23. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said crystalline substrate comprises silicon.

24. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said crystalline substrate comprises lithium niobate.

25. (Cancelled)

26. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said at least one cavity comprises a plurality of cavities.

27. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said microstructure comprises a micromechanical structure.

28. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said microstructure comprises a microelectronic structure.

29. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said microstructure comprises a optoelectronic structure.

30-32. (Cancelled)

33. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said crystalline substrate comprises lithium tantalate.

34. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said microstructure comprises a surface acoustic wave device.

35. (Cancelled)

36. (Original) A method of producing a crystalline substrate based device according to claim 20 and wherein said crystalline substrate comprises quartz.

37. (Cancelled)

38. (New) A method of producing a crystalline substrate based device according to claim 20 and wherein said spacer is formed as a piece separate from said at least one packaging layer.